

East : USPB, USPT, WPI D, JPO

L Number	Hits	Search Text	DB	Time stamp
1	12379	sti or (shallow with trench with isolat\$)	USPAT; US-PGPUB	2004/09/17 20:34
2	104	hdcvd or hpcvd or hdcvd	USPAT; US-PGPUB	2004/09/17 20:34
3	13411	ldpcvd or lpcvd or ldcvd	USPAT; US-PGPUB	2004/09/17 20:34
4	13614	high with cvd	USPAT; US-PGPUB	2004/09/17 20:35
5	13902	low with cvd	USPAT; US-PGPUB	2004/09/17 20:35
6	82726	chemical with (vapor or vapour) with deposition	USPAT; US-PGPUB	2004/09/17 20:35
7	8349	high with (chemical with (vapor or vapour) with deposition)	USPAT; US-PGPUB	2004/09/17 20:35
8	15990	low with (chemical with (vapor or vapour) with deposition)	USPAT; US-PGPUB	2004/09/17 20:32
9	85	(sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))	USPAT; US-PGPUB	2004/09/17 20:32
10	2329739	etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$	USPAT; US-PGPUB	2004/09/17 20:35
11	69	((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same (etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$)	USPAT; US-PGPUB	2004/09/17 20:34
12	31	((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same (mask or photomask or resist or photoresist)	USPAT; US-PGPUB	2004/09/17 20:36
14	3153	sti or (shallow with trench with isolat\$)	JPO; DERWENT	2004/09/17 20:34
15	4	hdcvd or hpcvd or hdcvd	JPO; DERWENT	2004/09/17 20:34
16	858	ldpcvd or lpcvd or ldcvd	JPO; DERWENT	2004/09/17 20:35
17	4759	high with cvd	JPO; DERWENT	2004/09/17 20:35
18	2849	low with cvd	JPO; DERWENT	2004/09/17 20:35
19	18010	chemical with (vapor or vapour) with deposition	JPO; DERWENT	2004/09/17 20:35
20	1812	high with (chemical with (vapor or vapour) with deposition)	JPO; DERWENT	2004/09/17 20:35
21	1300	low with (chemical with (vapor or vapour) with deposition)	JPO; DERWENT	2004/09/17 20:35
22	1804639	etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$	JPO; DERWENT	2004/09/17 20:36
23	306219	mask or photomask or resist or photoresist	JPO; DERWENT	2004/09/17 20:37
24	10	(sti or (shallow with trench with isolat\$)) and ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) and ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))	JPO; DERWENT	2004/09/17 20:37

25	8	((sti or (shallow with trench with isolat\$)) and ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) and ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) and ((etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$) or (mask or photomask or resist or photoresist))	JPO; DERWENT	2004/09/17 20:37
26	10	((sti or (shallow with trench with isolat\$)) and ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) and ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) or (((sti or (shallow with trench with isolat\$)) and ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) and ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) and ((etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$) or (mask or photomask or resist or photoresist)))	JPO; DERWENT	2004/09/17 20:38
13	85	((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) or (((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same (etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$)) or (((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same (mask or photomask or resist or photoresist))	USPAT; US-PGPUB	2004/09/17 20:45
27	25	((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) or (((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same (etch\$ or patern\$ or remov\$ or \$polish\$ or cmp or grind\$ or abrad\$ or planariz\$ or chemimech\$)) or (((sti or (shallow with trench with isolat\$)) same ((hdcvd or hpcvd or hdcvd) or (high with cvd) or (high with (chemical with (vapor or vapour) with deposition))) same ((ldpcvd or lpcvd or ldcvd) or (low with cvd) or (low with (chemical with (vapor or vapour) with deposition)))) same (mask or photomask or resist or photoresist)) and (sti or (shallow with trench\$ with isolat\$)).ti.	USPAT; US-PGPUB	2004/09/17 20:46

STN Caplus STN Columbus

FILE 'CAPLUS' ENTERED AT 19:57:59 ON 17 SEP 2004

L1 3250 S STI OR (SHALLOW WITH TRENCH? WITH ISOLAT?)
L2 596 S STIS
L3 3858 S LPCVD OR LCVD OR LOW(W) PRESSURE (W) CVD
L4 646 S LOW(W) PRESSURE (W) CHEMICAL (W) VAPOR (W) DEPOSITION
L5 52 S HPCVD OR HCVD OR HIGH(W) PRESSURE (W) CVD
L6 7 S HIGH(W) PRESSURE (W) CHEMICAL (W) VAPOR (W) DEPOSITION
L7 26 S (L1 OR L2) AND (L3 OR L4)
L8 1 S L7 AND (L5 OR L6)
L9 25 S L7 NOT L8
L10 9 S L9 AND HIGH AND PRESSURE
L11 16 S L9 NOT L10
L12 0 S L11 AND HP

(FILE 'HOME' ENTERED AT 20:18:05 ON 17 SEP 2004)

FILE 'CAPLUS' ENTERED AT 20:18:13 ON 17 SEP 2004

L1 0 S HDCVD
L2 2 S LDCVD
L3 79 S HDPCVD
L4 3236 S STI OR SHALLOW(W) TRENCH? (W) ISOLAT?
L5 28 S L3 AND L4
L6 3858 S LPCVD OR LCVD OR LOW(W) PRES? (W) CVD
L7 741 S LOW (W) PRES? (W) CHEMICAL (W) VAPOR (W) DEPOSIT?
L8 3 S L5 AND (L6 OR L7)